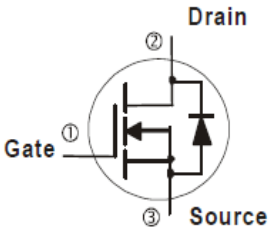
PJD50N10AL

100V N-Channel Enhancement Mode MOSFET

Voltage	100 V	Current	42 A

TO-252



Features

- $R_{DS(ON)}$, V_{GS}@10V, ID@20A<25mΩ
- $R_{DS(ON)}$, V_{GS}@4.5V, ID@15A<28.5mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case : TO-252 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0104 ounces, 0.297grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	42	A
	T_C=100°C		26	
Pulsed Drain Current (Note 1)	T_C=25°C	I_{DM}	150	
Power Dissipation	T_C=25°C	P_D	83	W
	T_C=100°C		33	
Continuous Drain Current	T_A=25°C	I_D	6.3	A
	T_A=70°C		5.1	A
Power Dissipation	T_A=25°C	P_D	2.0	W
Power Dissipation	T_A=70°C		1.3	
Single Pulse Avalanche Energy (Note 6)		E_{AS}	63.4	mJ
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~150	°C
Typical Thermal Resistance(Note 4,5)	Junction to Case	$R_{\theta JC}$	1.5	°C/W
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature

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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=20A	-	20	25	mΩ
		V_{GS}=4.5V,I_D=15A	-	22	28.5	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V	-	-	1.0	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	V_{DS}=50V, I_D=10A, V_{GS}=10V (Note 1,2)	-	29	-	nC
Gate-Source Charge	Q_{gs}		-	4.5	-	
Gate-Drain Charge	Q_{gd}		-	6.4	-	
Input Capacitance	Ciss	V_{DS}=30V, V_{GS}=0V, f=1.0MHZ	-	1485	-	pF
Output Capacitance	Coss		-	135	-	
Reverse Transfer Capacitance	Crss		-	67	-	
Turn-On Delay Time	$td_{(on)}$	V_{DD}=50V, I_D=10A, V_{GS}=10V, R_G=3Ω (Note 1,2)	-	7.8	-	ns
Turn-On Rise Time	t_r		-	30	-	
Turn-Off Delay Time	$td_{(off)}$		-	35	-	
Turn-Off Fall Time	t_f		-	14	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	42	A
Diode Forward Voltage	V_{SD}	I_S=1.0A, V_{GS}=0V	-	0.7	1.2	V

NOTES :

1. Pulse width≤300us, Duty cycle≤2%
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
4. The maximum current rating is package limited.
5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 $inch^2$ with 2oz.square pad of copper.
6. The test condition is L=3mH, I_{AS}=6.5A, V_{DD}=25V, V_{GS}=10V
7. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

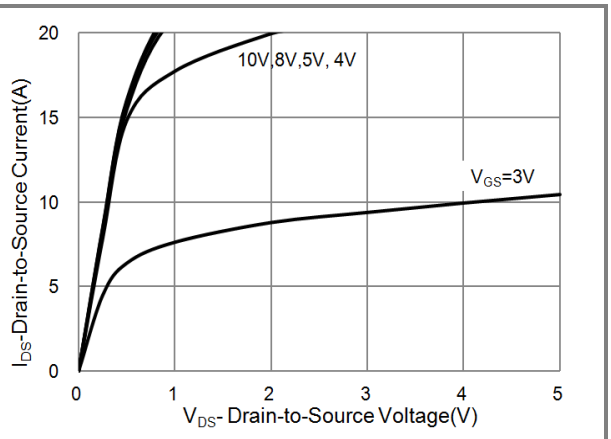

Fig.1 Output Characteristics

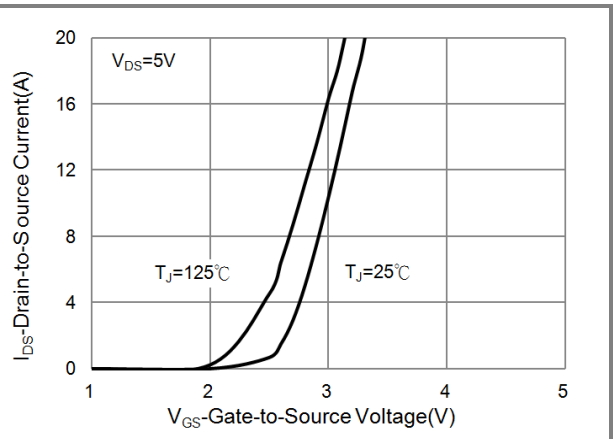

Fig.2 Transfer Characteristics

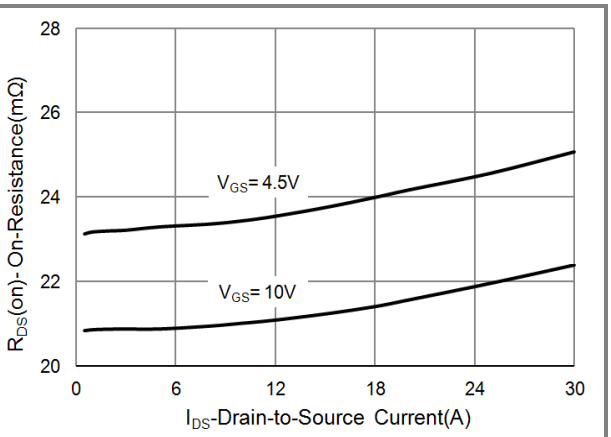

Fig.3 On-Resistance vs. Drain Current

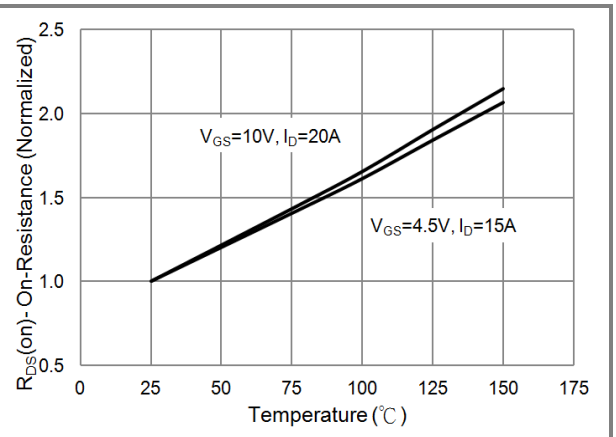

Fig.4 On-Resistance vs. Junction temperature

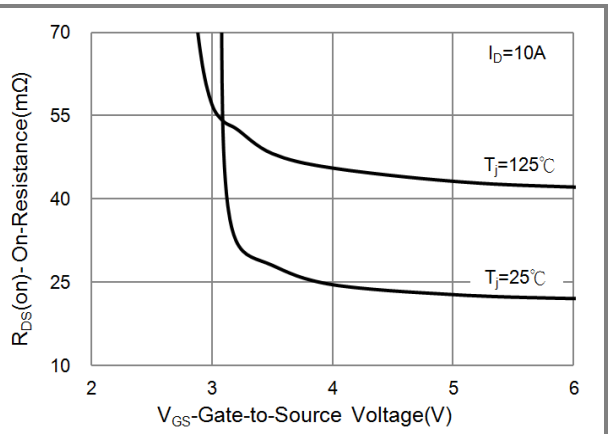

Fig.5 On-Resistance Variation with VGS.

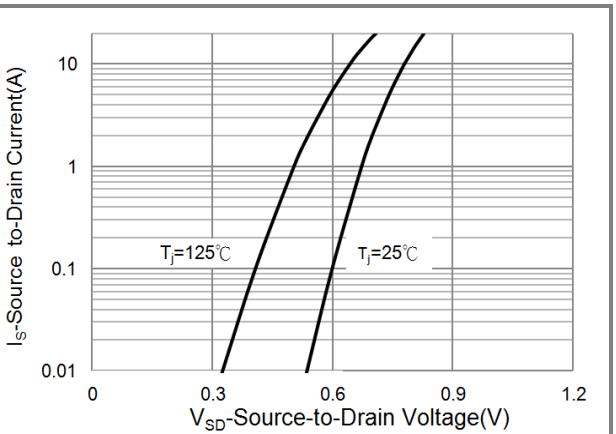

Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

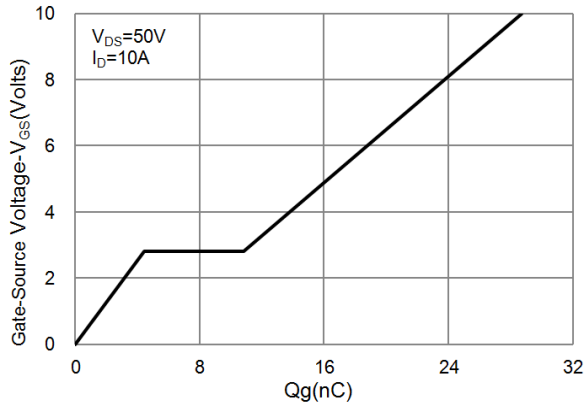

Fig.7 Gate-Charge Characteristics

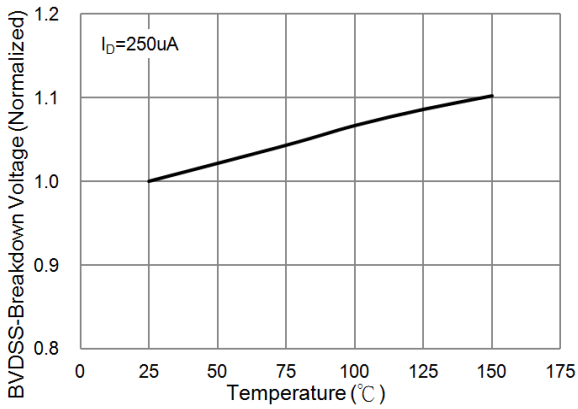

Fig.8 Breakdown Voltage Variation vs. Temperature

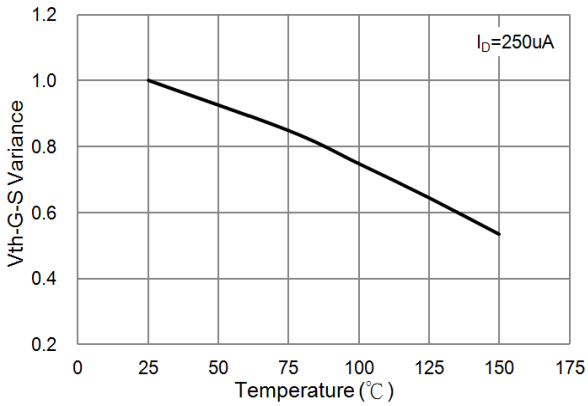

Fig.9 Threshold Voltage Variation with Temperature

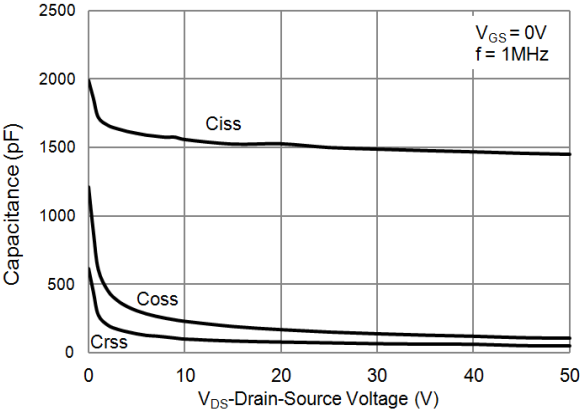

Fig.10 Capacitance vs. Drain-Source Voltage

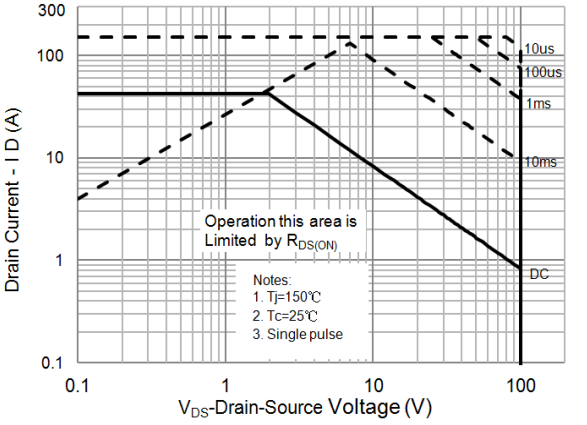

Fig.11 Maximum Safe Operating Area

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TYPICAL CHARACTERISTIC CURVES

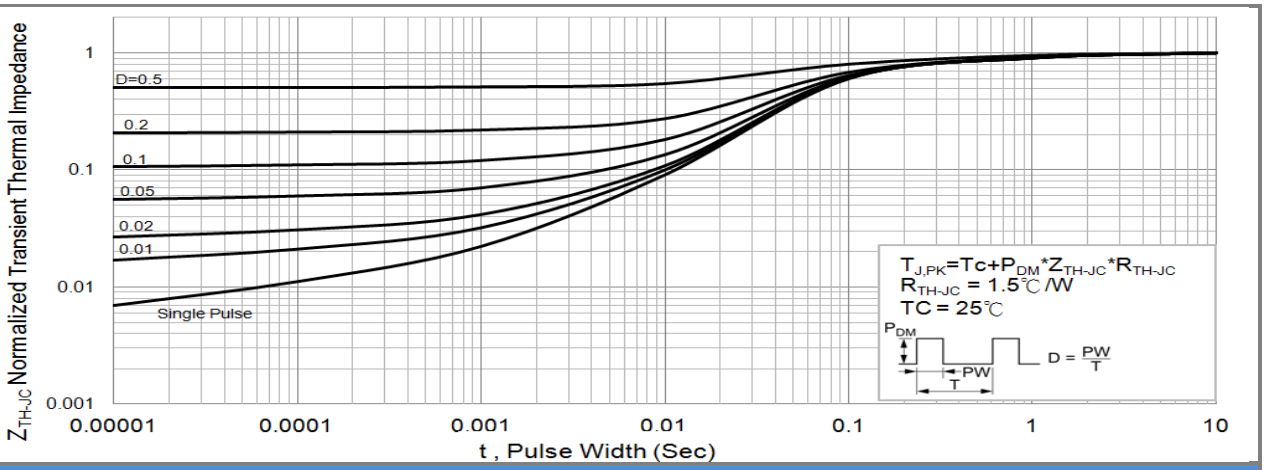
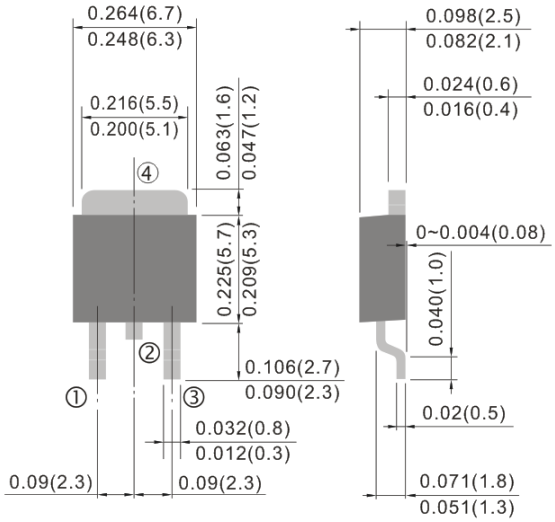


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

PJD50N10AL

Packaging Information .

TO-252 Dimension Unit: mm

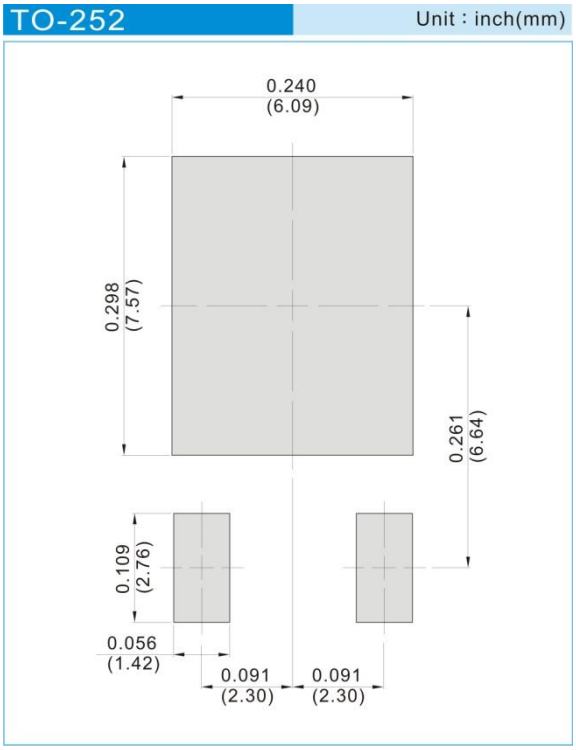


PJD50N10AL

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJD50N10AL_L2_00001	TO-252	3,000pcs / 13” reel	D50N10AL	Halogen free

MOUNTING PAD LAYOUT



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